

DA2JF8100L

Fast Recovery Diode DA2JF8100L

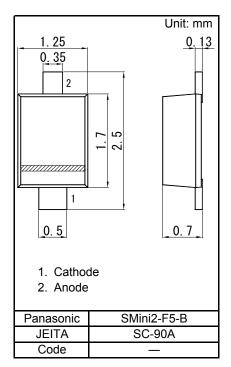
Silicon epitaxial planar type

For high speed switching circuits

- Features
- Small reverse current IR
- High repetitive peak reverse voltage VRRM
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 5A

Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)



Unit V V Internal Connection MA 2 MA 2 A 2 S0 °C S0 °C

■ Absolute Maximum Ratings Ta = 25 °C

| | - | | |
|--|--------|-------------|------|
| Parameter | Symbol | Rating | Unit |
| Repetitive peak reverse voltage | VRRM | 800 | V |
| Non-repetitive peak peak reverse voltage | VRSM | 800 | V |
| Forward current | IF | 200 | mA |
| Non-repetitive peak forward surge current *1,2 | IFSM | 1 | А |
| Junction temperature | Tj | -40 to +150 | °C |
| Operating ambient temperature | Topr | -40 to +85 | С° |
| Storage temperature | Tstg | -40 to +150 | С° |
| | | | |

Note) *1 Mounted on an alumina PC board

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Revised

: 2013-05-31

*2 50 Hz sine wave 1 cycle (Non-repetitive peak current)

Panasonic

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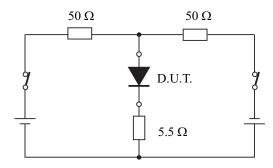
■ Electrical Characteristics Ta = 25 °C ± 3 °C

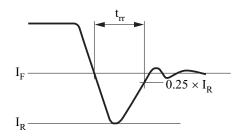
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit | |
|-------------------------------------|--------|-------------------------|-----|-----|-----|------|--|
| Forward voltage | VF | IF = 200 mA | | | 2.5 | V | |
| Reverse current | IRRM1 | VRRM = 400 V | | | 1 | μA | |
| | IRRM2 | VRRM = 800 V | | | 10 | μA | |
| Terminal capacitance | Ct | VR = 0 V, f = 1 MHz | | 0.6 | | pF | |
| Reverse recovery time ^{*1} | trr | IF = 100 mA, IR = 200mA | | 10 | 45 | ns | |
| | u | Irr = 0.25 x IR | | | 45 | | |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.
 2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the

charge of a human body and the leakage of current from the operating equipment.

3. *1 trr measurement circuit

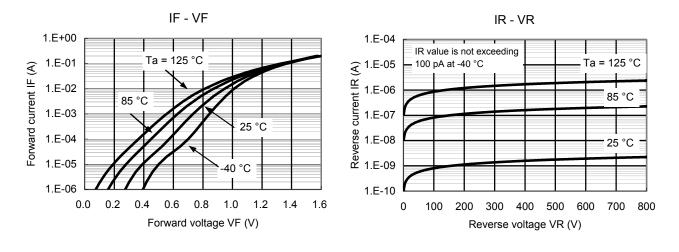


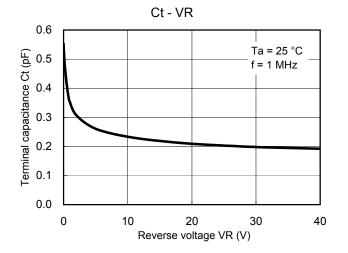




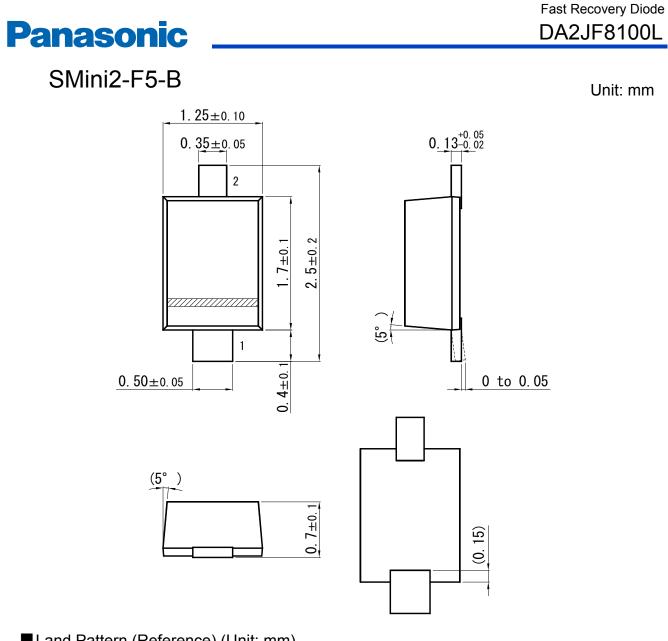
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Technical Data (reference)

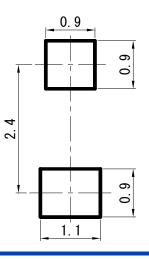




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Land Pattern (Reference) (Unit: mm)



Page 4 of 4

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